L Number	Hits	Search Text	DB	Time stamp
1	41267	"semiconductor memory" and "memory cell"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/07 16:35
2	97088	DRAM or (dynamic adj5 random adj5 access adj5 memory)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/07 16:04
3	13849	("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/07 16:04
4	6757	(("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/07 16:05
5	4822	((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 16:05
6	4	(((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/07 16:07
7	1828	array) and sub\$1decoder and gap (DRAM or (dynamic adj5 random adj5 access adj5 memory)) and PMOS and NMOS and "memory cell array"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 16:08
8	1259	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and PMOS and NMOS and "memory cell array") and transistor and well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 16:09
9	21	(((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and PMOS and NMOS and "memory cell array") and transistor and well) and sub\$ldecoder	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 16:14
10	790	cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07
11	684	cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array) and (sub\$ldecoder or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/07 16:33
14	79	pre\$1decoder)) and 365/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/07 16:35
15	15711	pre\$1decoder)) and 365/63.ccls. "semiconductor memory" near5 "memory cell"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 16:35

16	819	("semiconductor memory" near5 "memory cell") near5 (DRAM or (dynamic adj5	USPAT; US-PGPUB;	2004/06/07
	Ì	random adj5 access adj5 memory))	EPO; JPO;	10.31
			DERWENT;	
			IBM_TDB	0004405405
18	23	(("semiconductor memory" near5 "memory	USPAT; US-PGPUB;	2004/06/07
		cell") near5 (DRAM or (dynamic adj5 random adj5 access adj5 memory))) near10	EPO; JPO;	16:52
:		amplifier	DERWENT;	
1.0	23578	"memory cell" same row same column	IBM_TDB USPAT;	2004/06/07
19	235/8	memory ceri same row same corumn	US-PGPUB;	16:38
			EPO; JPO;	
			DERWENT;	
	0066	48	IBM_TDB	2004/06/07
20	2366	("memory.cell" same row same column) same substrate	USPAT; US-PGPUB;	2004/06/07
i		Substrate	EPO; JPO;	10.55
			DERWENT;	
	67	22.0	IBM_TDB	2004/06/07
22	67	(("memory cell" same row same column) same substrate) same amplifier same	USPAT; US-PGPUB;	2004/06/07
		"memory array"	EPO; JPO;	10.17
1			DERWENT;	
		12.0	IBM_TDB	2004/06/07
23	2	(("memory cell" same row same column) same substrate) same amplifier same	USPAT; US-PGPUB;	2004/06/07
		sub\$1decoder	EPO; JPO;	
			DERWENT;	
	450	n	IBM_TDB	2004/06/07
24	450	"sense amplifier driver"	USPAT; US-PGPUB;	2004/06/07
			EPO; JPO;	10.00
			DERWENT;	
28	9	"sense amplifier driver" and subdecoder	IBM_TDB USPAT;	2004/06/07
20	9	sense ampliller driver and subdecoder	US-PGPUB;	16:57
			EPO; JPO;	
			DERWENT;	
29	15	subdecoder near5 amplifier	IBM_TDB USPAT;	2004/06/07
23		Subdecoder Hears ampirite	US-PGPUB;	16:56
		·	EPO; JPO;	
			DERWENT;	
30	283	"sense amplifier driver" and decoder	IBM_TDB USPAT;	2004/06/07
	203	John Campillion all ver and account	US-PGPUB;	16:57
			EPO; JPO;	
			DERWENT; IBM TDB	
31	53	("sense amplifier driver" and decoder)	USPAT;	2004/06/07
		and gap and row and column	US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT;	
32	53	(("sense amplifier driver" and decoder)	USPAT;	2004/06/07
		and gap and row and column) and memory	US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT; IBM TDB	
34	41	((("sense amplifier driver" and decoder)	USPAT;	2004/06/07
		and gap and row and column) and memory)	US-PGPUB;	17:08
		and 365/\$7	EPO; JPO; DERWENT;	
			IBM TDB	
35	123	kawasaki-satoshi.in.	USPAT;	2004/06/07
			US-PGPUB;	17:08
			EPO; JPO; DERWENT;	
			IBM TDB	
	1	1		

36	1	kawasaki-satoshi-\$.in.	USPAT;	2004/06/07
		·	US-PGPUB;	17:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	